

# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L



ON Semiconductor®

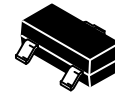
[www.onsemi.com](http://www.onsemi.com)

## VHF/UHF Transistor

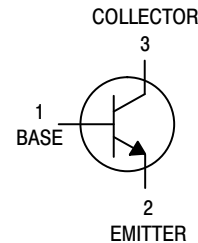
### NPN Silicon

#### Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SOT-23 (TO-236)  
CASE 318  
STYLE 6



#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	25	Vdc
Collector-Base Voltage	$V_{CBO}$	30	Vdc
Emitter-Base Voltage	$V_{EBO}$	3.0	Vdc

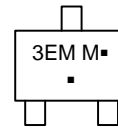
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

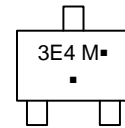
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina

#### MARKING DIAGRAMS



MMBTH10LT1G,  
NSVMMBTH10LT1G



MMBTH10-04LT1G

3EM, 3E4 = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10-4LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10LT3G, SMMBTH10-4LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C = 1.0 \text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CEO}$	25	-	-	Vdc
Collector-Base Breakdown Voltage ( $I_C = 100 \mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	30	-	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	3.0	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 25 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 2.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	-	100	nAdc

### ON CHARACTERISTICS

DC Current Gain ( $I_C = 4.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	$h_{FE}$	60 120	- -	- 240	-
Collector-Emitter Saturation Voltage ( $I_C = 4.0 \text{ mAdc}$ , $I_E = 0.4 \text{ mAdc}$ )	$V_{CE(sat)}$	-	-	0.5	Vdc
Base-Emitter On Voltage ( $I_C = 4.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ )	$V_{BE}$	-	-	0.95	Vdc

### SMALL-SIGNAL CHARACTERISTICS

Current-Gain – Bandwidth Product ( $I_C = 4.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 100 \text{ MHz}$ ) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	$f_T$	650 800	- -	- -	MHz
Collector-Base Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{cb}$	-	-	0.7	pF
Common-Base Feedback Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{rb}$	-	-	0.65	pF
Collector Base Time Constant ( $I_C = 4.0 \text{ mAdc}$ , $V_{CB} = 10 \text{ Vdc}$ , $f = 31.8 \text{ MHz}$ )	$r_b' C_c$	-	-	9.0	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

( $V_{CB} = 10 \text{ Vdc}$ ,  $I_C = 4.0 \text{ mA dc}$ ,  $T_A = 25^\circ\text{C}$ )

$y_{ib}$ , INPUT ADMITTANCE

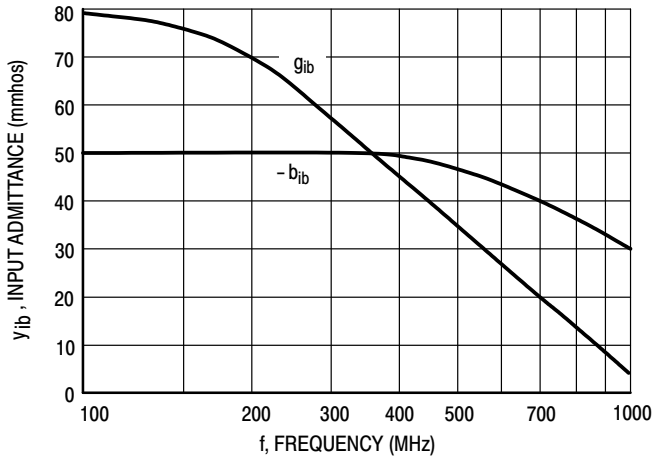


Figure 1. Rectangular Form

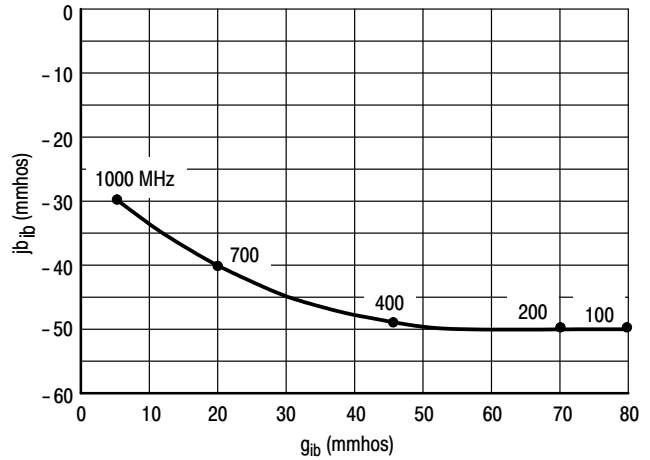


Figure 2. Polar Form

$y_{fb}$ , FORWARD TRANSFER ADMITTANCE

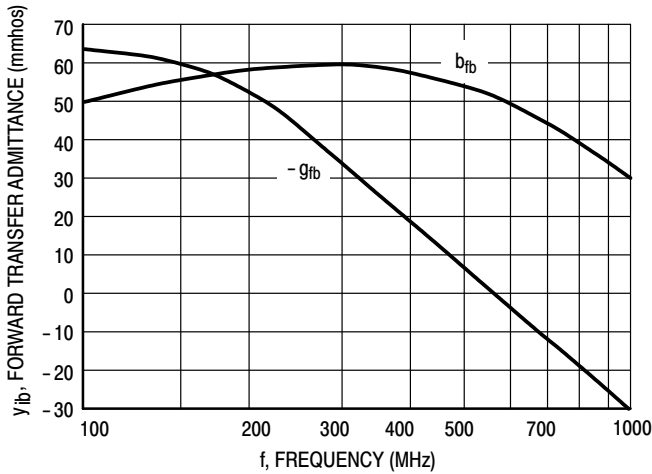


Figure 3. Rectangular Form

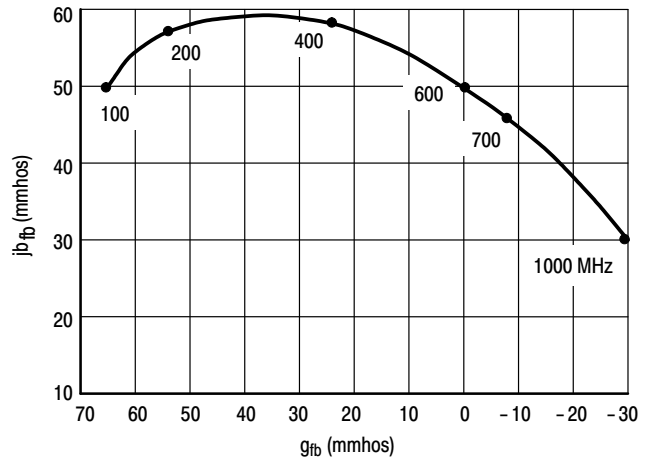


Figure 4. Polar Form

# MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

## TYPICAL CHARACTERISTICS

### COMMON-BASE $y$ PARAMETERS versus FREQUENCY

( $V_{CB} = 10$  Vdc,  $I_C = 4.0$  mAdc,  $T_A = 25^\circ\text{C}$ )

#### $y_{rb}$ , REVERSE TRANSFER ADMITTANCE

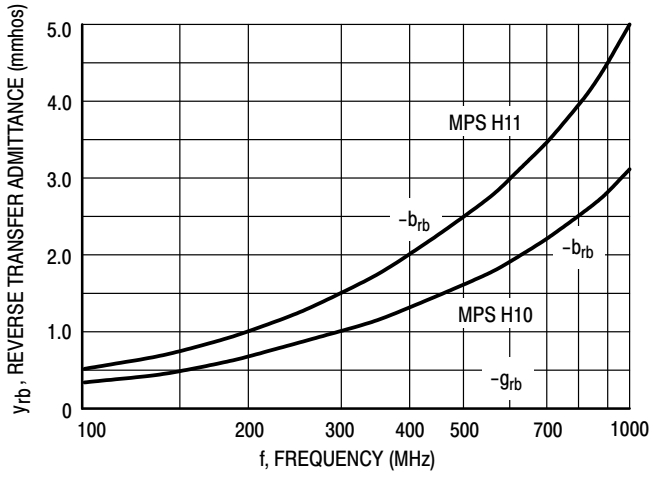


Figure 5. Rectangular Form

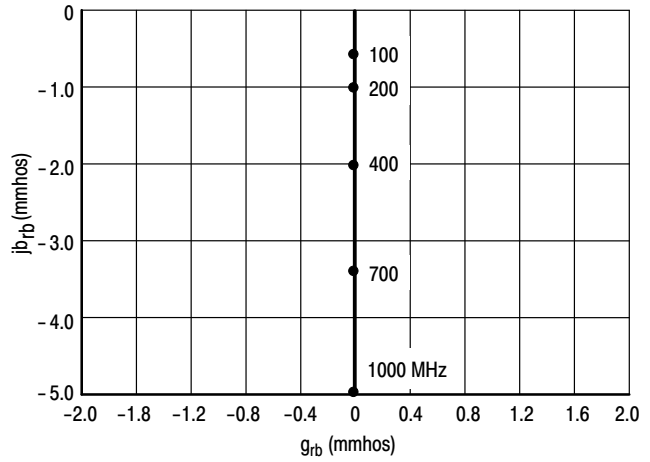


Figure 6. Polar Form

#### $y_{ob}$ , OUTPUT ADMITTANCE

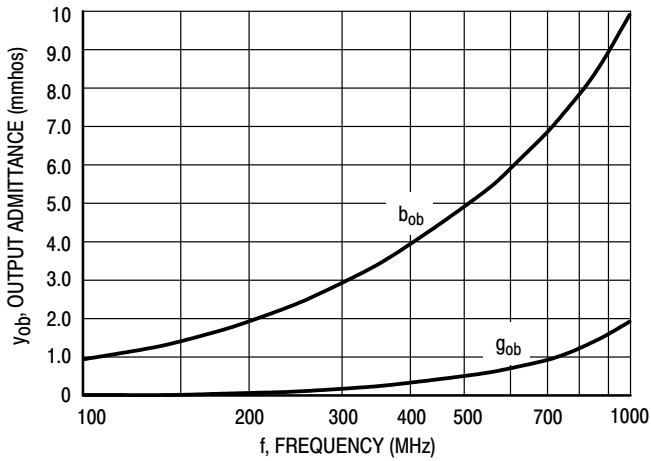


Figure 7. Rectangular Form

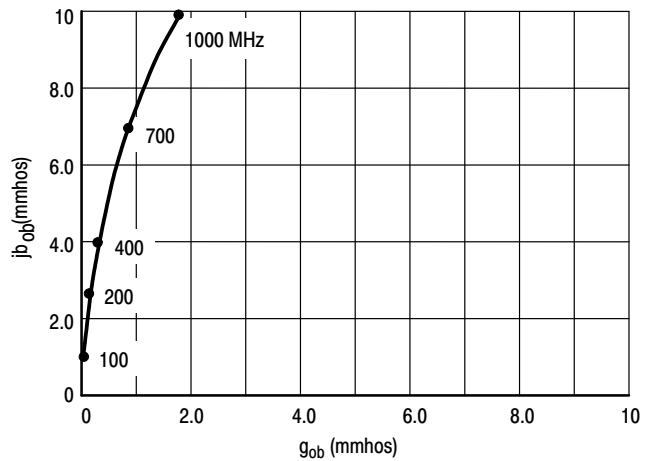


Figure 8. Polar Form

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

<b>DOCUMENT NUMBER:</b>	<b>98ASB42226B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

### Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## ON Semiconductor:

[MMBTH10-4LT1](#) [MMBTH10-4LT1G](#) [MMBTH10LT1](#) [MMBTH10LT1G](#) [NSVMMBTH10LT1G](#) [MMBTH10LT3G](#)  
[SMMBTH10-4LT3G](#)